

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

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Please amend the Specification beginning on page 1 line 13 and ending on page 2 line 7 as follows:

Positive photoresists for use in manufacturing processes of semiconductors must concurrently have different characteristics such as a characteristic that an exposed portion is made soluble in alkali by the application of light, adhesion to silicon wafers, plasma-etching resistance, and transparency to light used. The positive photoresists are generally used as a solution containing a base polymer, a light-activatable acid generator, and several types of additives for controlling the above characteristics. The wavelength of a light source for light irradiation in lithography for use in semiconductor manufacturing becomes shorter and shorter in recent years, and ArF excimer laser with a wavelength of 193 nm is promising as a next-generation light source. Various polymers containing a constitutional repeating unit having a group capable of partially leaving by the action of an acid to thereby become soluble in an alkali, and a constitutional repeating unit containing an alicyclic skeleton having a polar group have been proposed as resist polymers for use in the ArF excimer laser exposure system, for example in Japanese Unexamined Patent Application Publications No. 2000-26446 and ~~No. 09-73137~~ No. 09-73173.